

INFORMATION DISCLOSURE CITATION IN AN APPLICATION OCT 29 2003 (Use several sheets if necessary)				Document Number (Priority) TSMC-01-1388	Application Number 10/628,914	
				Applicant Chih-Ming Ke et al.		
				Filing Date 07/29/03	Drawn At U.S.	
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	SEARCH DATE IF APPROPRIATE
W	6 1 1 4 6 8	1/9/00	Komatsu	250	201.3	6/4/98
W	5 9 1 6 7 1	6/29/99	Butsch et al.	430	30	3/13/97
W	6 1 3 0 4 3 2	10/10/00	Pfeiffer et al.	250	396MI	4/13/99
W	5 0 2 5 1 6 5	6/18/91	Chen et al.	250	491.1	3/26/90
W	6 0 0 6 8 4 9 5	5/23/00	Masnaghetti et al.	250	310	9/8/98
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Page No., Etc.)						
W	"193 nm resist shrinkage", by Su et al., Solid State Technology May 2001, pp. 52-54 and 57.					
W	U.S. Patent Application Serial No. 10/047,266, Filed 1/14/02 "Reducing Photoresist Shrinkage via Plasma Treatment"					
W	assigned to the same assignee.					
EXAMINER	ZIA P. HASHMI	DATE CONSIDERED 6/29/04				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						